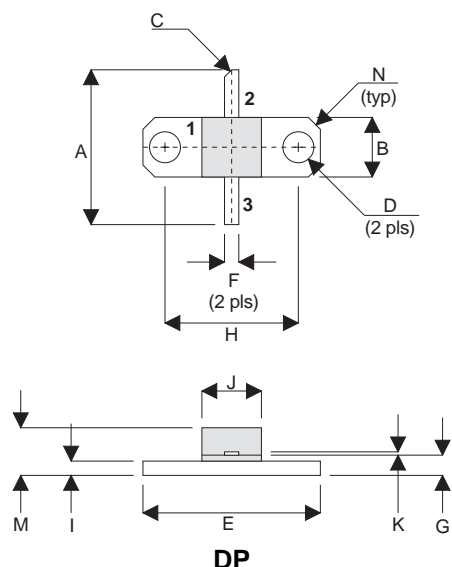


MECHANICAL DATA



PIN 1 SOURCE PIN 2 DRAIN
PIN 3 GATE

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
M	5.08	0.51	0.200	0.020
N	1.27 x 45°	0.13	0.050 x 45°	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 20W – 28V – 500MHz SINGLE ENDED

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- USEFUL P_O AT 1GHz
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	50W
BV_{DSS}	Drain – Source Breakdown Voltage	70V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	5A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 100mA	70			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 28V V _{GS} = 0			1	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 1A	0.8			S
G _{PS} Common Source Power Gain	P _O = 20W	13			dB
η Drain Efficiency	V _{DS} = 28V I _{DQ} = 0.2A	50			%
VSWR Load Mismatch Tolerance	f = 500MHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 28V V _{GS} = –5V f = 1MHz			60	pF
C _{oss} Output Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			30	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			2.5	pF
R _{dson} Saturation Resistance	V _{GS} = 20V I _{DS} = 2.5A		1		Ω

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 3.5°C / W
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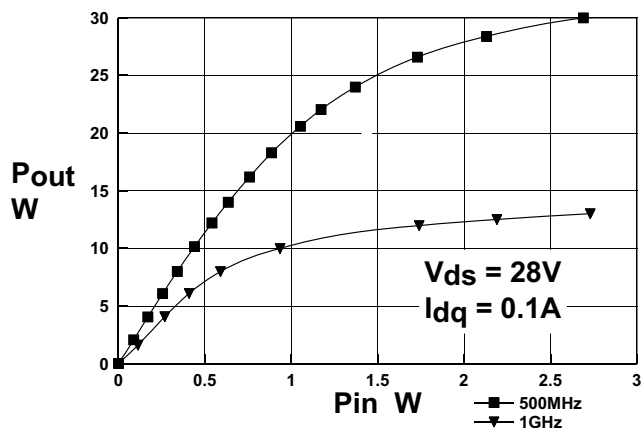


Figure 1
Power Output vs. Input Power

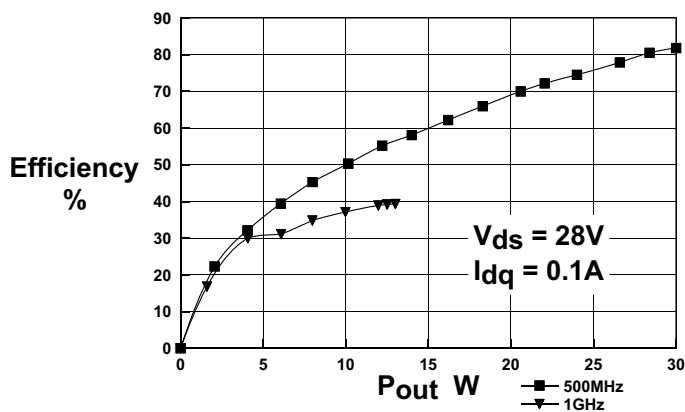


Figure 2
Efficiency vs. Output Power

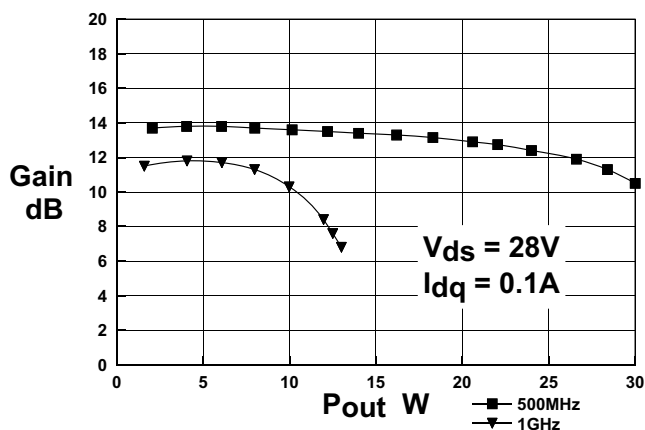


Figure 3
Gain vs. Output Power

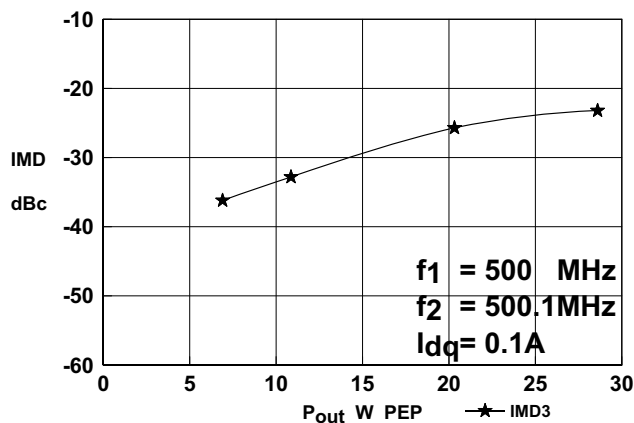


Figure 4
IMD vs. Output Power

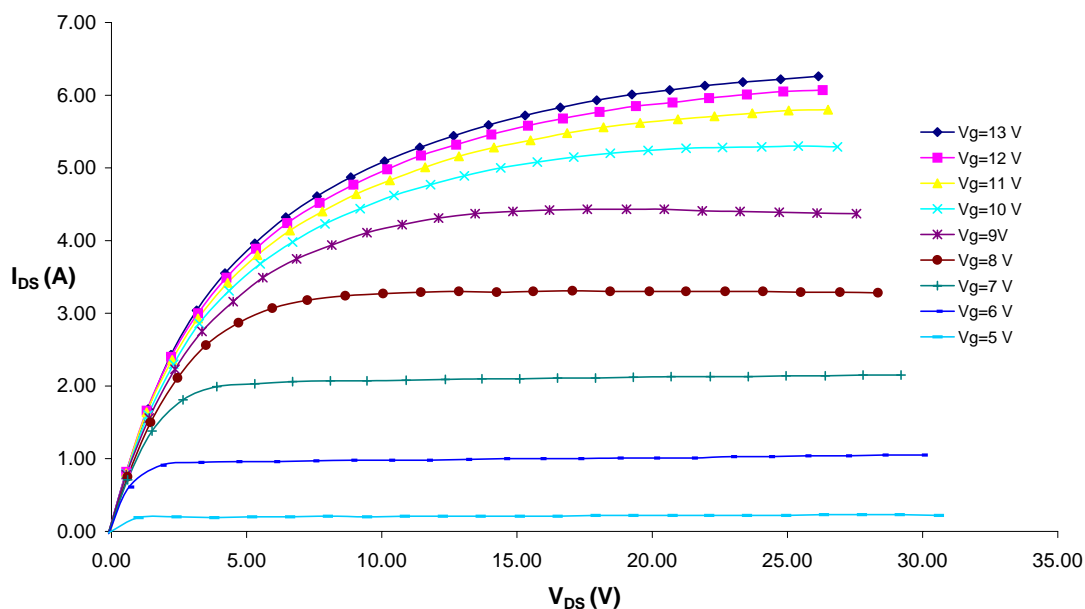


Figure 5 – Typical IV Characteristics.

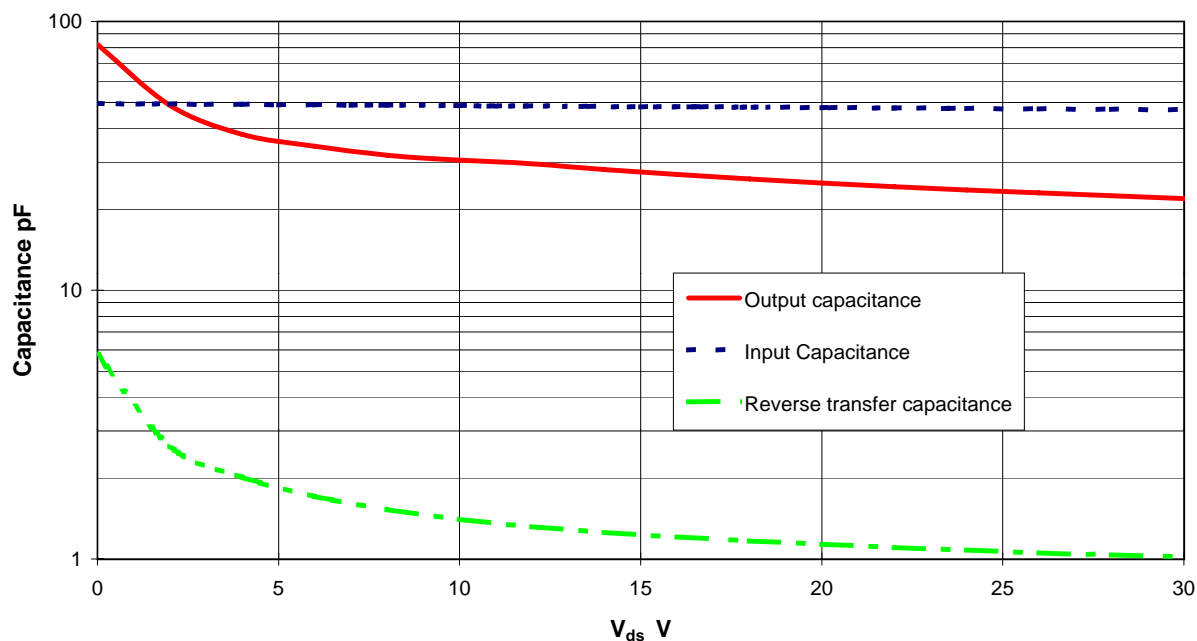
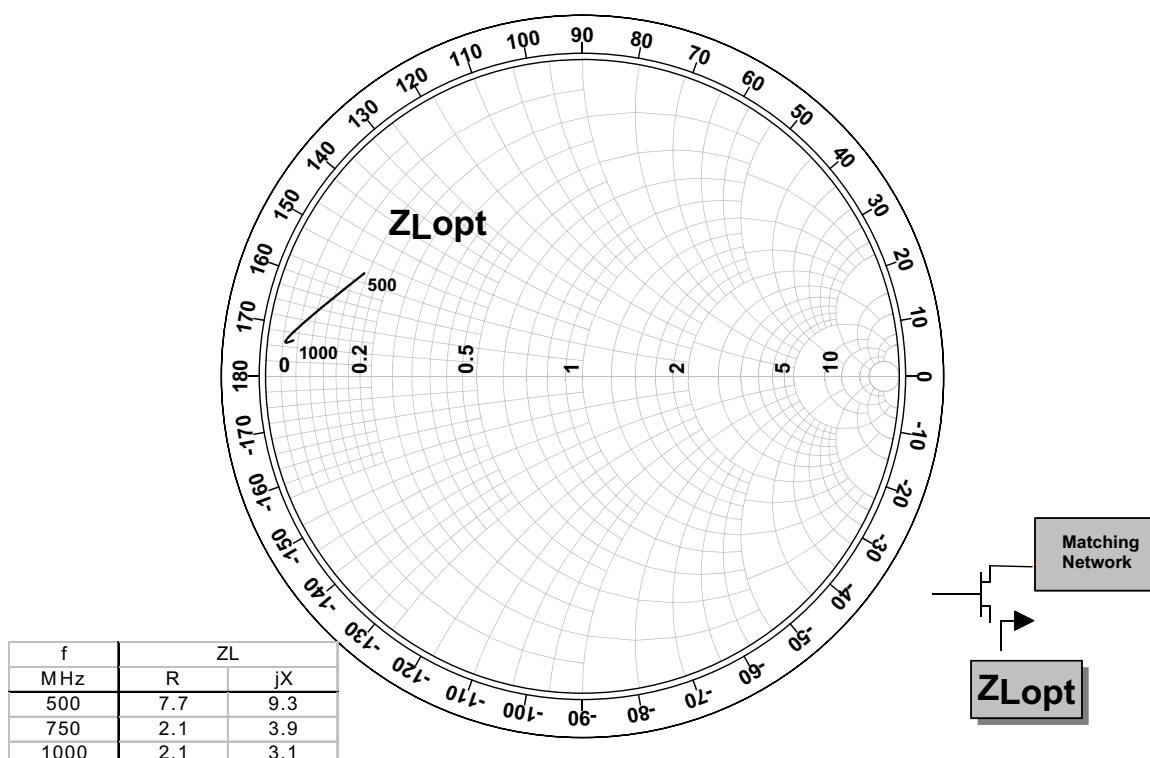
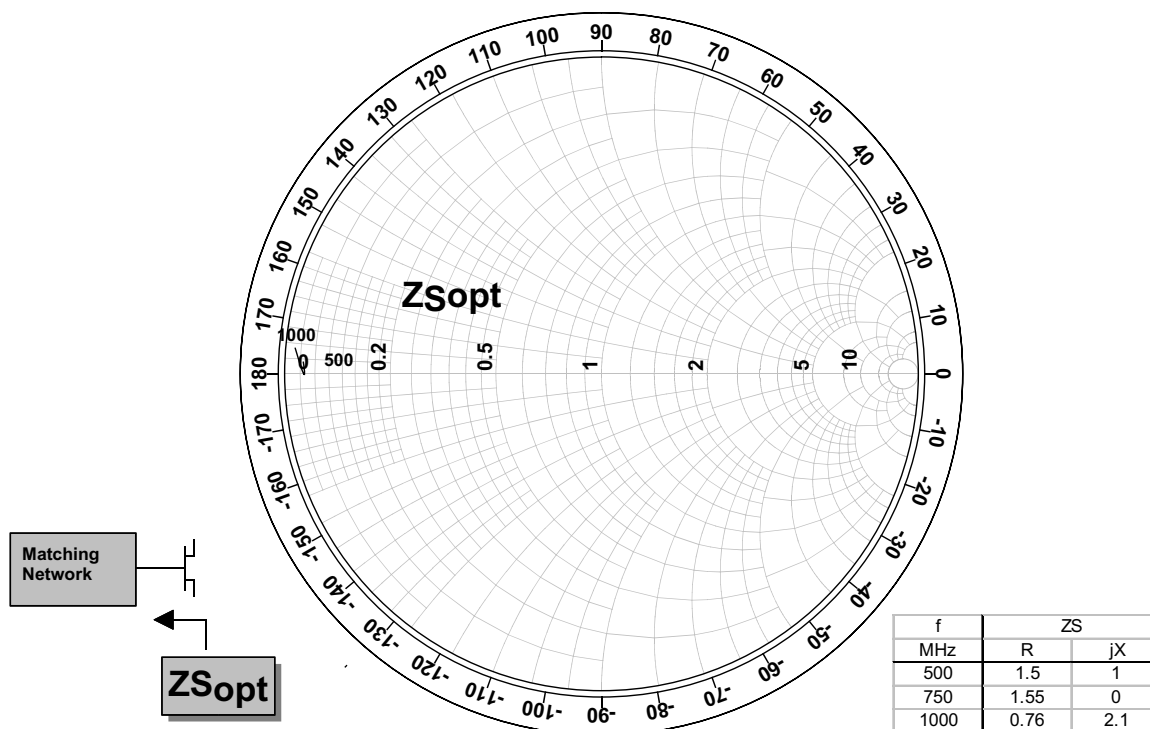
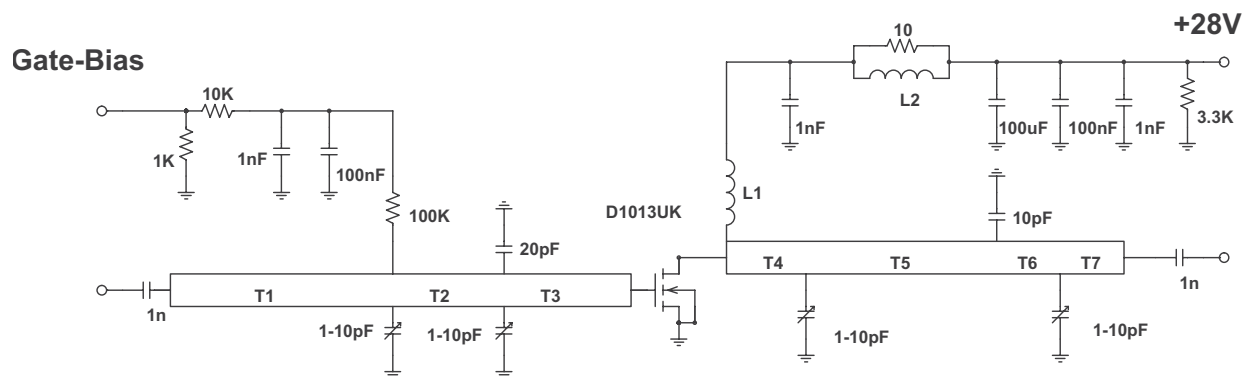


Figure 6 – Typical CV Characteristics.



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500MHz Test Fixture

Substrate 0.8 mm FR4, $\epsilon_r = 2.2$

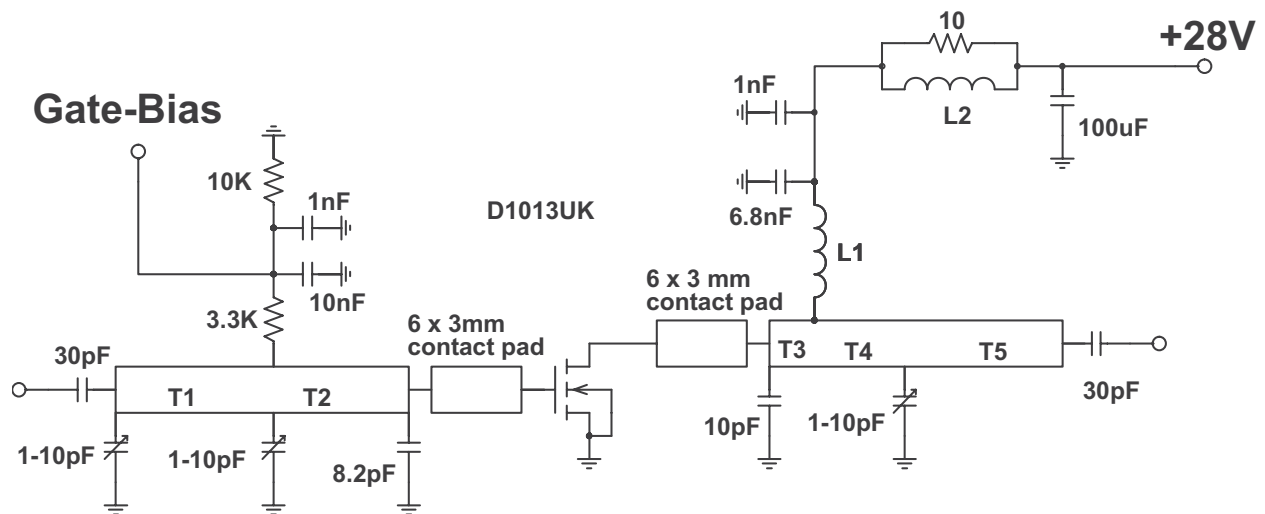
All microstrip lines $W = 2.2\text{mm}$

T1
T2
T3 10mm
T4
T5 30mm
T6 6mm
T7 12.5mm

L1 5.5 turns 20swg enamelled copper wire 7mm i.d.

L2 1.5 turns 24swg enamelled copper wire on Siemens B62152A7X 2 hole

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1GHz Test Fixture

Substrate 0.8mm PTFE/glass, $\epsilon_r = 2.5$

All microstrip lines $W = 2.2\text{mm}$

T1	35mm
T2	15mm
T3	4mm
T4	14mm
T5	32mm

L1	7.5 turns 24swg enamelled copper wire 3mm i.d.
L2	1.5 turns 24swg enamelled copper wire on ferrite core

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